

**SANYO**

No.4114

**2SK1806**

N-Channel Junction Silicon FET

Low-Frequency General-Purpose  
Amp Applications Impedance conversion**Features**

- Low frequency amplifiers, impedance conversion, ideal for potentiometers, analog switches, and constant current supplies.

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain to Source Voltage	V <sub>DSX</sub>	30	V
Gate to Drain Voltage	V <sub>GDS</sub>	-30	V
Gate Current	I <sub>G</sub>	10	mA
Drain Current	I <sub>D</sub>	20	mA
Allowable Power Dissipation	P <sub>D</sub>	250	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
G-D Breakdown Voltage	V <sub>(BR)GDS</sub>	I <sub>G</sub> = -10 μA, V <sub>DS</sub> = 0	-30			V
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = -20V, V <sub>DS</sub> = 0			-1.0	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1 μA	-0.2	-0.7	-2.5	V
Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0	0.6*		6.0*	mA
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1kHz	2.5	5.0		mS
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz		5.0		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz		1.5		pF
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	V <sub>DS</sub> = 10mV, V <sub>GS</sub> = 0		250		Ω

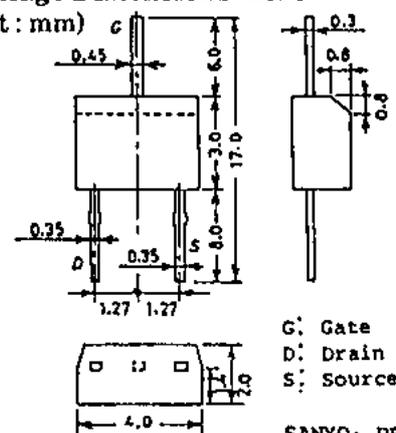
\* : The 2SK1806 is classified by I<sub>DSS</sub> as follows (unit: mA)

0.6	C	1.5	1.2	D	3.0	2.5	E	6.0
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Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

**Package Dimensions 2026**

(unit: mm)

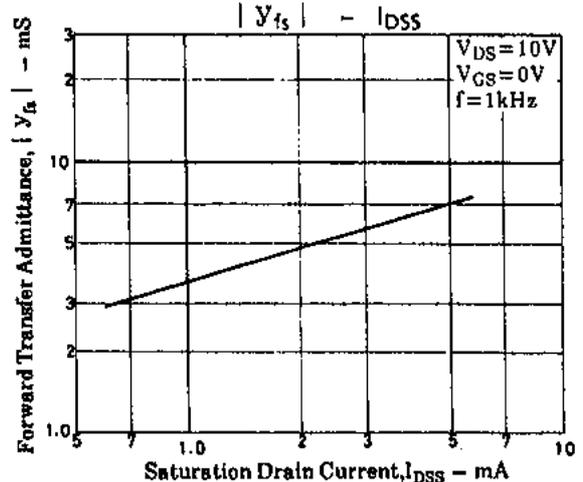
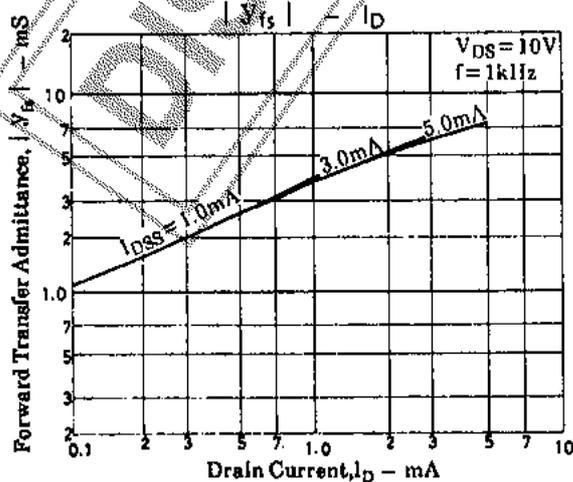
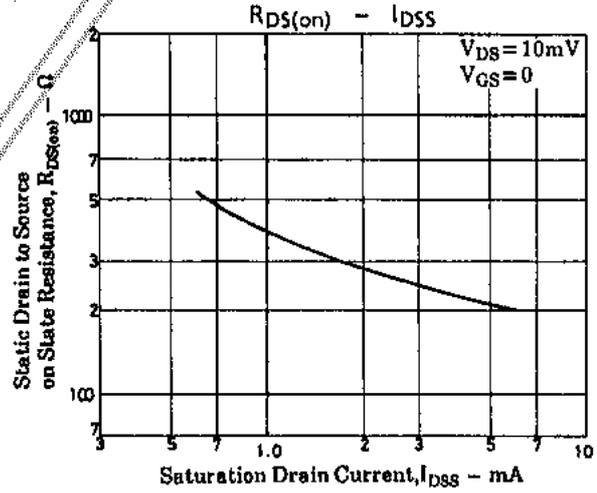
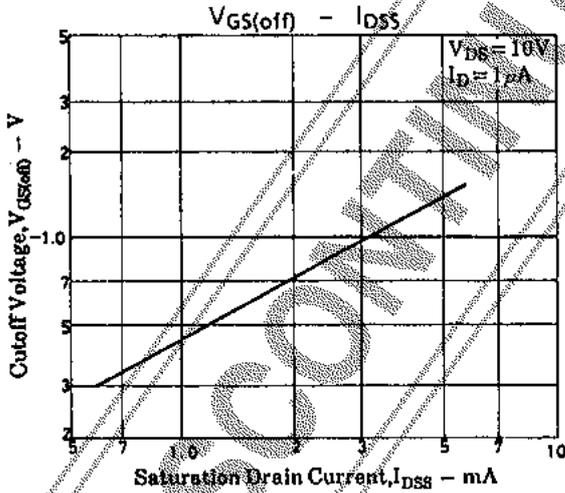
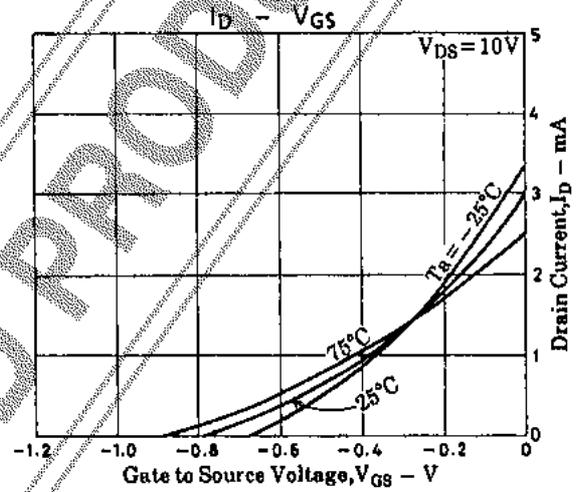
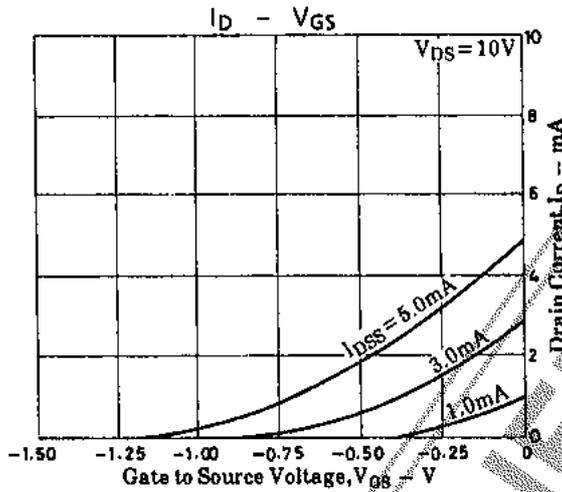
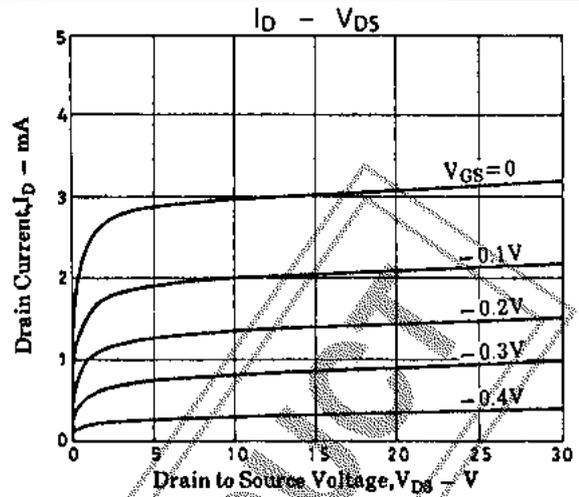
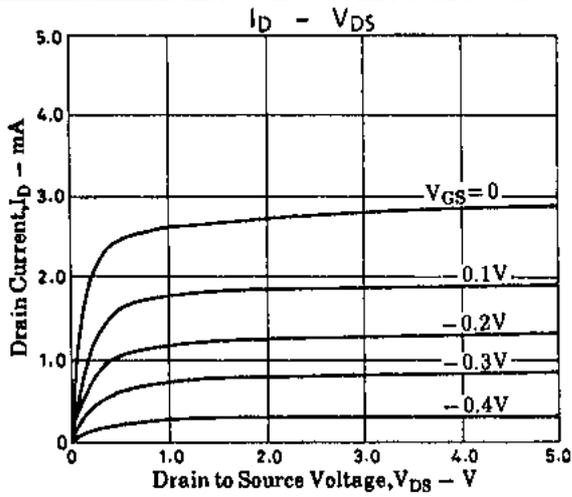


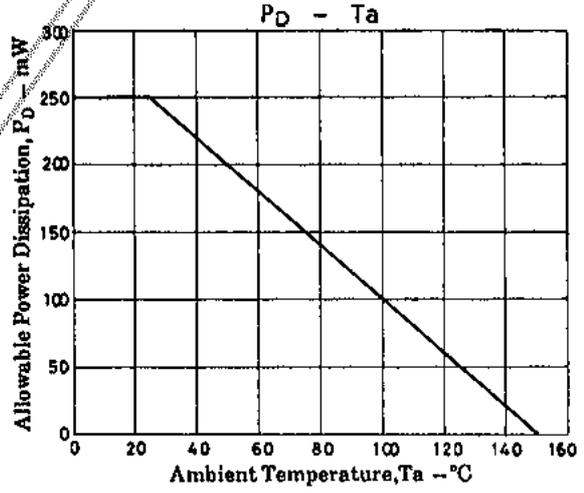
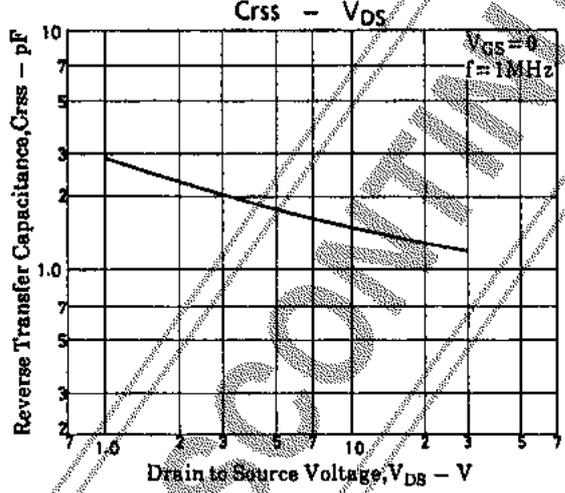
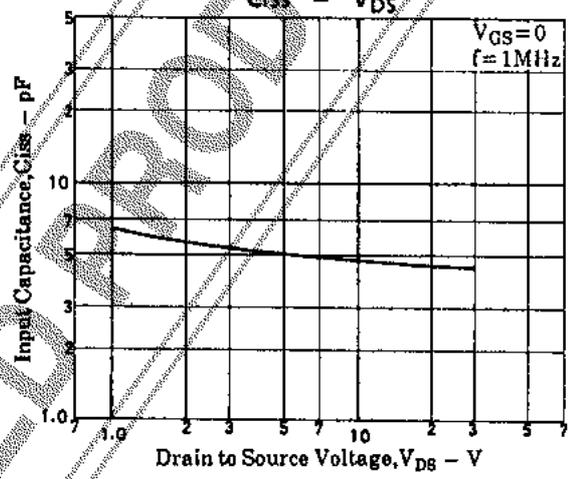
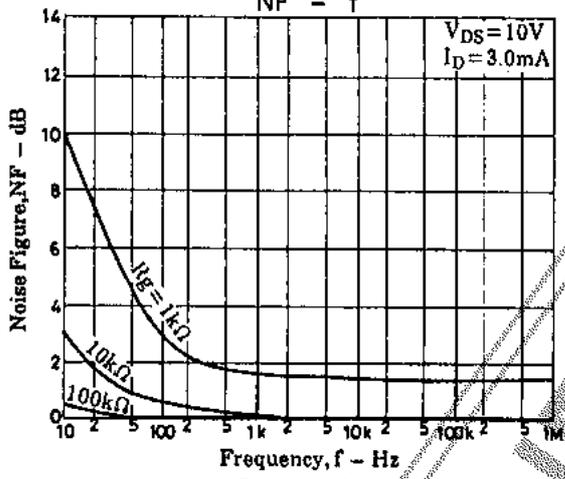
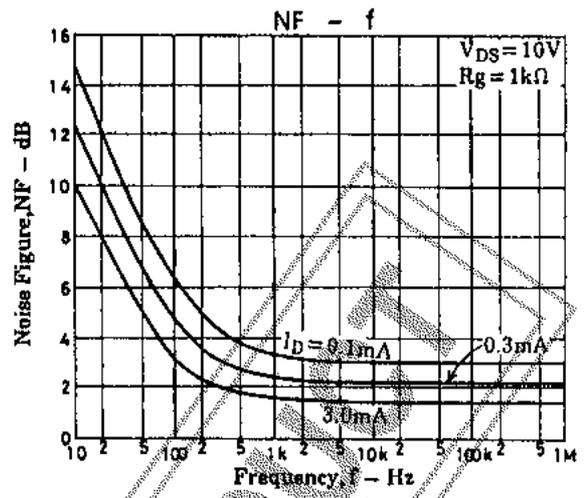
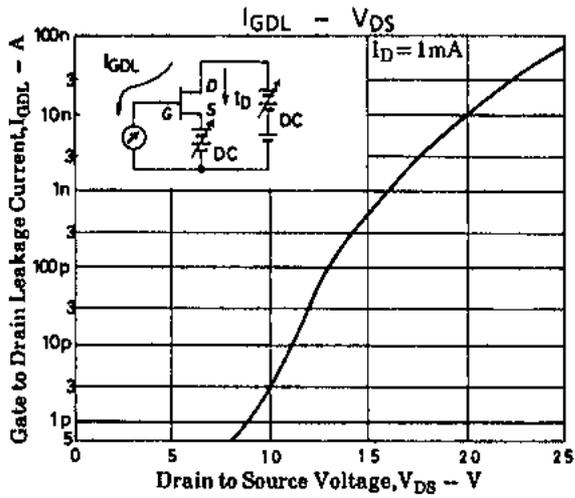
SANYO: DP3

Specifications and information herein are subject to change without notice.

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DISCONTINUED PRODUCT